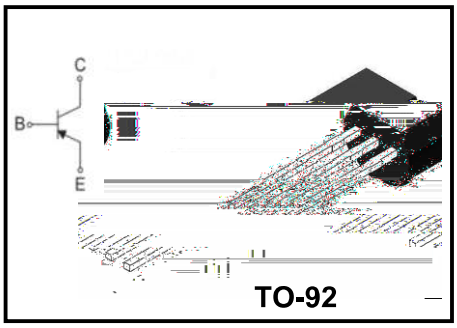

Parameter	Symbol	Value	Unit
Collector-Base Voltage	BV_{CBO}	-40	V
Collector-Emitter Voltage	BV_{CEO}	-30	V
Emitter-Base Voltage	BV_{EBO}	-5	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55～＋150	°C

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Collector-base breakdown voltage	BV_{CBO}	I_C = -100μA，I_E = 0	-40			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C = -1mA，I_B = 0	-20			V
Emitter-base breakdown voltage	BV_{EBO}	I_E = -100μA，I_C = 0	-5			V
Collector cut-off current	I_{CBO}	V_{CB} = -25V，I_E = 0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB} = -3V，I_C = 0			-100	nA
DC current gain	$h_{FE}1$	V_{CE} = -1V，I_C = -50mA	64		350	
	$h_{FE}2$	V_{CE} = -1V，I_C = -500mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -500mA，I_B = -50mA			0.6	V
Base -emitter saturation voltage	$V_{BE(sat)}$	I_C = -500mA，I_B = -50mA			1.2	V



Figure 1. Static Characteristic

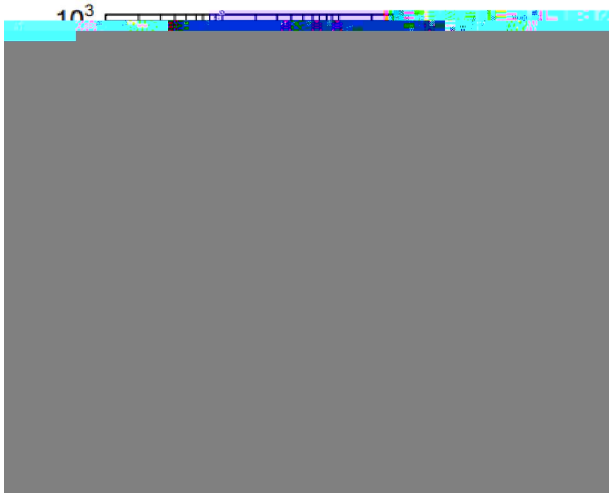

Figure 2. DC current Gain

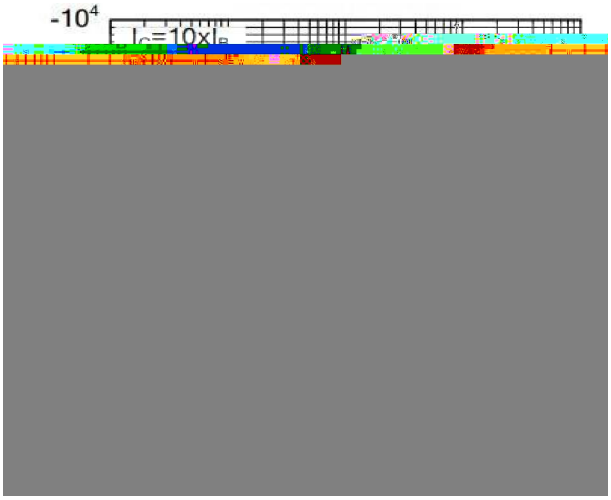

Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

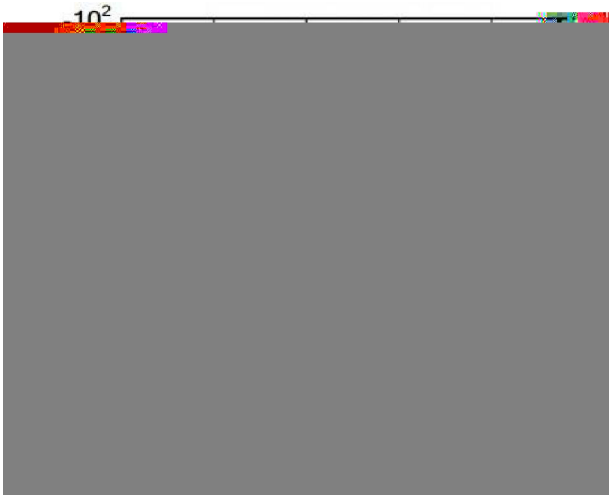

Figure 4. Base-Emitter On Voltage



Figure 5. Collector Output Capacitance

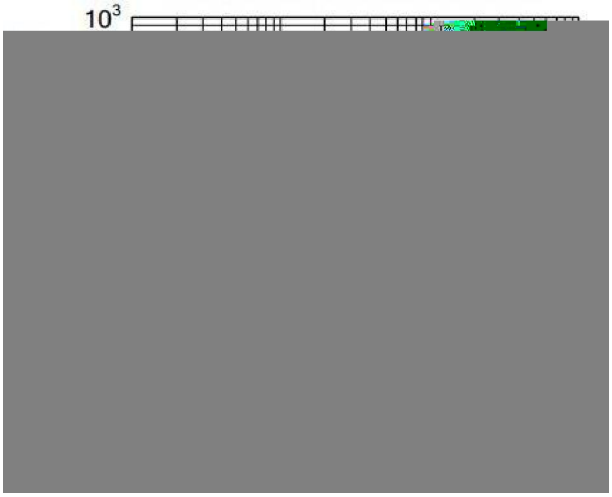

Figure 6. Current Gain Bandwidth Product

Ordering in